DIELECTRIC STRENGTH OF INSULATING MATERIALS

L. I. Berger

The loss of the dielectric properties by a sample of a gaseous, liquid, or solid insulator as a result of application to the sample of an electric field* greater than a certain critical magnitude is called *dielectric breakdown.* The critical magnitude of electric field at which the breakdown of a material takes place is called the *dielectric strength* of the material (or *breakdown voltage*). The dielectric strength of a material depends on the specimen thickness (as a rule, thin films have greater dielectric strength than that of thicker samples of a material), the electrode shape**, the rate of the applied voltage increase, the shape of the voltage vs. time curve, and the medium surrounding the sample, e.g., air or other gas (or a liquid — for solid materials only).

Breakdown in Gases

The current carriers in gases are free electrons and ions generated by external radiation. The equilibrium concentration of these particles at normal pressure is about 10^3 cm^{-3}, and hence the electrical conductivity is very small, of the order of 10^{-16} - 10^{-15} S/cm. But in a strong electric field, these particles acquire kinetic energy along their free pass, large enough to ionize the gas molecules. The new charged particles ionize more molecules; this avalanche-like process leads to formation between the electrodes of channels of conducting plasma (streamers), and the electrical resistance of the space between the electrodes decreases virtually to zero.

Because the dielectric strength (breakdown voltage) of gases strongly depends on the electrode geometry and surface condition and the gas pressure, it is generally accepted to present the data for a particular gas as a fraction of the dielectric strength of either nitrogen or sulfur hexafluoride measured at the same conditions. In Table 1, the data are presented in comparison with the dielectric strength of nitrogen, which is considered equal to 1.00. For convenience to the reader, a few average magnitudes of the dielectric strength of some gases are expressed in kilovolts per millimeter. The data in the table relate to the standard conditions, unless indicated otherwise.

Breakdown in Liquids

If a liquid is pure, the breakdown mechanism in it is similar to that in gases. If a liquid contains liquid impurities in the form of small drops with greater dielectric constant than that of the main liquid, the breakdown is the result of formation of ellipsoids from these drops by the electric field. In a strong enough electric field, these ellipsoids merge and form a high-conductivity channel between the electrodes. The current increases the temperature in the channel, liquid boils, and the current along the steam canal leads to breakdown. Formation of a conductive channel (bridge) between the electrodes is observed also in liquids with solid impurities. If a liquid contains gas impurities in the form of small bubbles, breakdown is the result of heating of the liquid in strong electric fields. In the locations with the highest current density, the liquid boils, the size of the gas bubbles increases, they merge and form gaseous channels between the electrodes, and the breakdown medium is again the gas plasma.

Breakdown in Solids

It is known that the current in solid insulators does not obey Ohm's law in strong electric fields. The current density increases almost exponentially with the electric field, and at a certain field magnitude it jumps to very high magnitudes at which a specimen of a material is destroyed. The two known kinds of electric breakdown are thermal and electrical breakdowns. The former is the result of material heating by the electric current. Destruction of a sample of a material happens when, at a certain voltage, the amount of heat produced by the current exceeds the heat release through the sample surface; the breakdown voltage in this case is proportional to the square root of the ratio of the thermal conductivity and electrical conductivity of the material. The electrical breakdown results from the tunneling of the charge carriers from electrodes or from the valence band or from the impurity levels into the conduction band, or by the impact ionization. The tunnel effect breakdown happens mainly in thin layers, e.g., in thin p-n junctions. Otherwise, the impact ionization mechanism dominates. For this mechanism, the dielectric strength of an insulator can be estimated using Boltzmann's kinetic equation for electrons in a crystal.

In the following tables, the dielectric strength values are for room temperature and normal atmospheric pressure, unless indicated otherwise.

* The unit of electric field in the SI system is newton per coulomb or volt per meter.

** For example, the U.S. standard ASTM D149 is based on use of symmetrical electrodes, while per U.K. standard BS2918 one electrode is a plane and the other is a rod with the axis normal to the plane.

Table 1
Dielectric Strength of Gases

Material	Dielectric* Strength	Ref.
Nitrogen, N_2	1.00	
Hydrogen, H_2	0.50	1,2
Helium, He	0.15	1
Oxygen, O_2	0.92	2
Air	0.97	6
Air (flat electrodes), kV/mm	3.0	3
Air, kV/mm	0.4-0.7	4
Air, kV/mm	1.40	5
Neon, Ne	0.25	1
	0.16	2
Argon, Ar	0.18	2
Chlorine, Cl_2	1.55	1
Carbon monoxide, CO	1.02	1
	1.05	2
Carbon dioxide, CO_2	0.88	1
	0.82	2
	0.84	6
Nitrous oxide, N_2O	1.24	2
Sulfur dioxide, SO_2	2.63	2
	2.68	6
Sulfur monochloride, S_2Cl_2 (at 12.5 Torr)	1.02	1
Thionyl fluoride, SOF_2	2.50	1
Sulfur hexafluoride, SF_6	2.50	1
	2.63	2
Sulfur hexafluoride, SF_6, kV/mm	8.50	7
	9.8	8
Perchloryl fluoride, ClO_3F	2.73	1
Tetrachloromethane, CCl_4	6.33	1
	6.21	2
Tetrafluoromethane, CF_4	1.01	1
Methane, CH_4	1.00	1
	1.13	2
Bromotrifluoromethane, CF_3Br	1.35	1
	1.97	2
Bromomethane, CH_3Br	0.71	2
Chloromethane, CH_3Cl	1.29	2
Iodomethane, CH_3I	3.02	2
Iodomethane, CH_3I, at 370 Torr	2.20	7
Dichloromethane, CH_2Cl_2	1.92	2
Dichlorodifluoromethane, CCl_2F_2	2.42	1
	2.63	2,6
Chlorotrifluoromethane, $CClF_3$	1.43	1
	1.53	2

Material	Dielectric* Strength	Ref.
Trichlorofluoromethane, CCl_3F	3.50	1
	4.53	2
Trichloromethane, $CHCl_3$	4.2	1
	4.39	2
Methylamine, CH_3NH_2	0.81	1
Difluoromethane, CH_2F_2	0.79	2
Trifluoromethane, CHF_3	0.71	2
Bromochlorodifluoromethane, CF_2ClBr	3.84	2
Chlorodifluoromethane, $CHClF_2$	1.40	1
	1.11	2
Dichlorofluoromethane, $CHCl_2F$	1.33	1
	2.61	2
Chlorofluoromethane, CH_2ClF	1.03	1
Hexafluoroethane, C_2F_6	1.82	1
	2.55	2
Ethyne (Acetylene), C_2H_2	1.10	1
	1.11	2
Chloropentafluoroethane, C_2ClF_5	2.3	1
	3.0	6
Dichlorotetrafluoroethane, $C_2Cl_2F_4$	2.52	1
Chlorotrifluoroethylene, C_2ClF_3	1.82	2
1,1,1-Trichloro-2,2,2-trifluoroethane	6.55	2
1,1,2-Trichloro-1,2,2-trifluoroethane	6.05	2
Chloroethane, C_2H_5Cl	1.00	1
1,1-Dichloroethane	2.66	2
Trifluoroacetonitrile, CF_3CN	3.5	1
Acetonitrile, CH_3CN	2.11	2
Dimethylamine, $(CH_3)_2NH$	1.04	1
Ethylamine, $C_2H_5NH_2$	1.01	1
Ethylene oxide (oxirane), CH_3CHO	1.01	1
Perfluoropropene, C_3F_6	2.55	2
Octafluoropropane, C_3F_8	2.19	1
	2.47	2
3,3,3-Trifluoro-1-propene, CH_2CHCF_3	2.11	2
Pentafluoroisocyanoethane, C_2F_5NC	4.5	1
1,1,1,4,4,4-Hexafluoro-2-butyne, CF_3CCCF_3	5.84	2
Octafluorocyclobutane, C_4F_8	3.34	2
1,1,1,2,3,4,4,4-Octafluoro-2-butene	2.8	1
Decafluorobutane, C_4F_{10}	3.08	1
Perfluorobutanenitrile, C_3F_7CN	5.5	1
Perfluoro-2-methyl-1,3-butadiene, C_5F_8	5.5	1
Hexafluorobenzene, C_6F_6	2.11	2
Perfluorocyclohexane, C_6F_{12}, (saturated vapor)	6.18	2

*Relative to nitrogen, unless units of kV/mm are indicated.

Table 2
Dielectric Strength of Liquids

Material	Dielectric strength kV/mm	Ref.
Helium, He, liquid, 4.2 K	10	9
Static	10	11
Dynamic	5	11
	23	12
Nitrogen, N_2, liquid, 77K		
Coaxial cylinder electrodes	20	10
Sphere to plane electrodes	60	10
Water, H_2O, distilled	65-70	13
Carbon tetrachloride, CCl_4	5.5	14
	16.0	15
Hexane, C_6H_{14}	42.0	16
Two 2.54 cm diameter spherical electrodes, 50.8 μm space	156	17,18
Cyclohexane, C_6H_{12}	42-48	16
2-Methylpentane, C_6H_{14}	149	17,18
2,2-Dimethylbutane, C_6H_{14}	133	17,18
2,3-Dimethylbutane, C_6H_{14}	138	17,18
Benzene, C_6H_6	163	17,18
Chlorobenzene, C_6H_5Cl	7.1	14
	18.8	15
2,2,4-Trimethylpentane, C_8H_{18}	140	17,18
Phenylxylylethane	23.6	19
Heptane, C_7H_{16}	166	17,18
2,4-Dimethylpentane, C_7H_{16}	133	17,18
Toluene, $C_6H_5CH_3$	199	17,18
	46	16
	12.0	14
	20.4	15
Octane, C_8H_{18}	16.6	14
	20.4	15
	179	17,18
Ethylbenzene, C_8H_{10}	226	17,18
Propylbenzene, C_9H_{12}	250	17,18
Isopropylbenzene, C_9H_{12}	238	17,18
Decane, $C_{10}H_{22}$	192	17,18
Butylbenzene, $C_{10}H_{14}$	275	17,18
Isobutylbenzene, $C_{10}H_{14}$	222	17,18
Silicone oils—polydimethylsiloxanes, $(CH_3)_3Si\text{-}O\text{-}[Si(CH_3)_2]_x\text{-}O\text{-}Si(CH_3)_3$		
Polydimethylsiloxane silicone fluid	15.4	20
Dimethyl silicone	24.0	21,22
Phenylmethyl silicone	23.2	22
Silicone oil, Basilone M50	10-15	23
Mineral insulating oils	11.8	6
Polybutene oil for capacitors	13.8	6
Transformer dielectric liquid	28-30	6
Isopropylbiphenyl capacitor oil	23.6	6
Transformer oil	110.7	24
Transformer oil Agip ITE 360	9-12.6	23
Perfluorinated hydrocarbons		
Fluorinert FC 6001	8.0	23
Fluorinert FC 77	10.7	23
Perfluorinated polyethers		
Galden XAD (Mol. wt. 800)	10.5	23
Galden D40 (Mol. wt. 2000)	10.2	23
Castor oil	65	25

Table 3
Dielectric Strength of Solids

Material	Dielectric strength kV/mm	Ref
Sodium chloride, NaCl, crystalline	150	26
Potassium bromide, KBr, crystalline	80	26
Ceramics		
Alumina (99.9% Al_2O_3)	13.4	6,27a
Aluminum silicate, Al_2SiO_5	5.9	6
Berillia (99% BeO)	13.8	6,27b
Boron nitride, BN	37.4	6
Cordierite, $Mg_2Al_4Si_5O_{18}$	7.9	6,27c
Forsterite, Mg_2SiO_4	9.8	28
Porcelain	35-160	26
Steatite, $Mg_3Si_4O_{11}\cdot H_2O$	9.1-15.4	6
Titanates of Mg, Ca, Sr, Ba, and Pb	20-120	3
Barium titanate, glass bonded	>30	36
Zirconia, ZrO_2	11.4	29
Glasses		
Fused silica, SiO_2	470-670	26
Alkali-silicate glass	200	26
Standard window glass	9.8-13.8	28
Micas		
Muscovite, ruby, natural	118	6
Phlogopite, amber, natural	118	6
Fluorophlogopite, synthetic	118	6
Glass-bonded mica	14.0-15.7	6
Thermoplastic Polymers		
Polypropylene	23.6	6
Amide polymer nylon 6/6, dry	23.6	6
Polyamide-imide copolymer	22.8	6
Modified polyphenylene oxide	21.7	6
Polystyrene	19.7	6
Polymethyl methacrylate	19.7	6
Polyetherimide	18.9	6
Amide polymer nylon 11(dry)	16.7	6
Polysulfone	16.7	6
Styrene-acrylonitrile copolymer	16.7	6
Acrylonitrile-butadiene-styrene	16.7	6
Polyethersulfone	15.7	6
Polybutylene terephthalate	15.7	6
Polystyrene-butadiene copolymer	15.7	6
Acetal homopolymer	15.0	6
Acetal copolymer	15.0	6

Table 3
Dielectric Strength of Solids (continued)

Material	Dielectric strength kV/mm	Ref.
Polyphenylene sulfide	15.0	6
Polycarbonate	15.0	6
Acetal homopolymer resin (molding resin)	15.0	6
Acetal copolymer resin	15.0	6
Thermosetting Molding Compounds		
Glass-filled allyl (Type GDI-30 per MIL-M-14G)	15.7	6
Glass-filled epoxy, electrical grade	15.4	6
Glass-filled phenolic (Type GPI-100 per MIL-M-14G)	15.0	6
Glass-filled alkyd/polyester (Type MAI-60 per MIL-M-14G)	14.8	6
Glass-filled melamine (Type MMI-30 per MIL-M-14G)	13.4	6
Extrusion Compounds for High-Temperature Insulation		
Polytetrafluoroethylene	19.7	6
Perfluoroalkoxy polymer	21.7	6
Fluorinated ethylene-propylene copolymer	19.7	6
Ethylene-tetrafluoroethylene copolymer	15.7	6
Polyvinylidene fluoride	10.2	6
Ethylene-chlorotrifluoroethylene copolymer	19.3	6
Polychlorotrifluoroethylene	19.7	6
Extrusion Compounds for Low-Temperature Insulation		
Polyvinyl chloride		
Flexible	11.8-15.7	30
Rigid	13.8-19.7	30
Polyethylene	18.9	28
Polyethylene, low-density	21.7	6
	300	31
Polyethylene, high-density	19.7	6
Polypropylene/polyethylene copolymer	23.6	6
Embedding Compounds		
Basic epoxy resin: bisphenol-A/epichlorohydrin polycondensate	19.7	6
Cycloaliphatic epoxy: alicyclic diepoxy carboxylate	19.7	6
Polyetherketone	18.9	30
Polyurethanes		
Two-component, polyol-cured	25.4	6
Two-part solventless, polybutylene-based	24.0	6
Silicones		
Clear two-part heat curing eletrical grade silicone embedding resin	21.7	6
Red insulating enamel (MIL-E-22118)		
Dry	47.2	6
Wet	11.8	6
Enamels		
Red enamel, fast cure		
Standard conditions	78.7	6
Immersion conditions	47.2	6
Black enamel		
Standard conditions	70.9	6
Immersion conditions	47.2	6
Varnishes		
Vacuum-pressure impregnated baking type solventless polyester varnish		
Rigid, two-part	70.9	6
Semiflexible high-bond thixotropic	78.7	6
Rigid high-bond high-flash freon-resistant	68.9	6
Baking type epoxy varnish		
Solventless, rigid, low viscosity, one-part	90.6	6
Solventless, semiflexible, one-part	82.7	6
Solventless, semirigid, chemical resistant, low dielectric constant	106.3	6
Solvable, for hermetic electric motors	181.1	6
Polyurethane coating		
Clear conformal, fast cure		
Standard conditions	78.7	6
Immersion conditions	47.2	6
Insulating Films and Tapes		
Low-density polyethylene film (40 μm thick)	300	31
Poly-*p*-xylylene film	410-590	32
Aromatic polymer films		
Kapton H (Du Pont)	389-430	33
Ultem (GE Plastic and Roem AG)	437-565	33
Hostaphan (Hoechst AG)	338-447	33
Amorphous Stabar K2000 (ICI film)	404-422	33
Stabar S100 (ICI film)	353-452	33
Polyetherimide film (26 μm)	486	34
Parylene N/D (poly-*p*-xylylene/poly-dichloro-*p*-xylylene) 25 μm film	275	6
Cellulose acetate film	157	6
Cellulose triacetate film	157	6
Polytetrafluoroethylene film	87-173	6
Perfluoroalkoxy film	157-197	6
Fluorinated ethylene-propylene copolymer film	197	6
Ethylene-tetrafluoroethylene film	197	6
Ethylene-chlorotrifluoroethylene copolymer film	197	6
Polychlorotrifluoroethylene film	118-153.5	6
High-voltage rubber insulating tape	28	6
Various Insulators		
Rubber, natural	100-215	26
Butyl rubber	23.6	6
Neoprene	15.7-27.6	6
Silicone rubber	26-36	6
Room-temperature vulcanized silicone rubber	9.2-10.9	35
Ureas (from carbamide to tetraphenylurea)	11.8-15.7	28
Dielectric papers		
Aramid paper, calendered	28.7	6
Aramid paper, uncalendered	12.2	6
Aramid with Mica	39.4	6

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